ABSTRACT

METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

Provided is a semiconductor device which can reduce leakage of current between wirings. Included steps are forming a first insulator over a first conductor which is formed over substrate; forming a first hard mask thereover; forming a first resist mask comprising a first opening, over the first hard mask; etching the first hard mask to form a second hard mask comprising a second opening; etching the first insulator using the second hard mask to form a second insulator comprising a third opening; forming a second conductor embedded in the second opening and the third opening; performing polishing treatment on the second hard mask and the second conductor to form a third conductor embedded in the third opening; forming a fourth conductor thereover; forming a second resist mask in a pattern over the fourth conductor; and dry-etching the fourth conductor to form a fifth conductor. The second hard mask can be dry-etched.

~~Fig. 4~~

Fig. 4A